

Pb Free Plating Product

GF3035MG thru GF30200MG



30.0 Ampere Surface Mount PhotoVoltaic Bypass Schottky Barrier Rectifier

Features

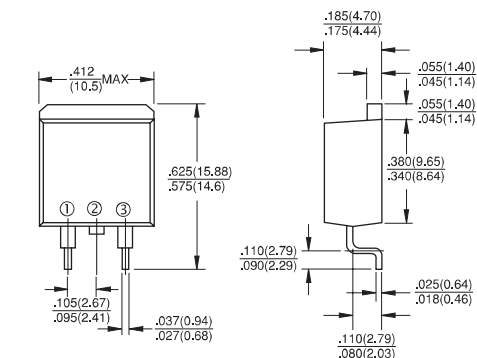
- ✧ Plastic material used carries Underwriters Laboratory Classifications 94V-0
- ✧ Metal silicon junction, majority carrier conduction
- ✧ Low power loss, high efficiency
- ✧ High current capability, low forward voltage drop
- ✧ High surge capability
- ✧ For use in low voltage, high frequency inverters, free wheeling, and polarity protection applications
- ✧ Guardring for overvoltage protection
- ✧ High temperature soldering guaranteed: 260°C/10 seconds, 0.25" (6.35mm) from case

Mechanical Data

- ✧ Cases: JEDEC TO-263/D2PAK molded plastic body
- ✧ Terminals: Pure tin plated, lead free. solderable per MIL-STD-750, Method 2026
- ✧ Polarity: As marked
- ✧ Mounting position: Any
- ✧ Mounting torque: 5 in. - lbs. max
- ✧ Weight: 0.08 ounce, 2.24 grams

TO-263

Unit: inch (mm)



LEFT PIN ①
RIGHT PIN ③

② BOTTOM SIDE
HEAT SINK

Note: Pins Left & Right must be electrically connected at the printed circuit board.

Maximum Ratings and Electrical Characteristics

Rating at 25 °C ambient temperature unless otherwise specified.

Single phase, half wave, 60 Hz, resistive or inductive load.

For capacitive load, derate current by 20%

Type Number	Symbol	GF30-35MG	GF30-45MG	GF30-50MG	GF30-60MG	GF30-90MG	GF30-100MG	GF30-200MG	Units
Maximum Recurrent Peak Reverse Voltage	V _{RRM}	35	45	50	60	90	100	200	V
Maximum RMS Voltage	V _{RMS}	24	31	35	42	63	70	140	V
Maximum DC Blocking Voltage	V _{DC}	35	45	50	60	90	100	200	V
Maximum Average Forward Rectified Current at Tc=125°C	I _(AV)	30							A
Peak Repetitive Forward Current (Rated V _R , Square Wave, 20KHz) at Tc=125°C	I _{FRM}	58							A
Peak Forward Surge Current, 8.3 ms Single Half Sine-wave Superimposed on Rated Load (JEDEC method)	I _{FSM}	250							A
Peak Repetitive Reverse Surge Current (Note 1)	I _{RRM}	1.0		0.5				A	
Maximum Instantaneous Forward Voltage at: (Note 2) I _F =30A, T _C =25°C I _F =30A, T _C =125°C	V _F	0.63 0.57	0.75 0.65		0.85 0.75		0.95 0.92	V	
Maximum Instantaneous Reverse Current @Tc=25 °C at Rated DC Blocking Voltage (Note 2) @ Tc=125 °C	I _R	0.8 15	0.8 10		0.8 7.5		0.8 5	mA mA	
Voltage Rate of Change (Rated V _R)	dV/dt	10,000							V/uS
Typical Junction Capacitance	C _j	600							pF
Maximum Typical Thermal Resistance(Note 3)	R _{θJC}	2.5							°C/W
Operating Junction Temperature Range	T _J	-65 to +150							°C
Storage Temperature Range	T _{STG}	-65 to +175							°C

Notes: 1. 2.0 μs Pulse Width, $f=1.0\text{ KHz}$
 2. Pulse Test: 300 μs Pulse Width, 1% Duty Cycle
 3. Thermal Resistance from Junction to Case Per Leg with Heatsink Size of 2" x 3" x 0.25" Al-Plate.

RATINGS AND CHARACTERISTIC CURVES(GF3035MG thru GF30200MG)

FIG.1- FORWARD CURRENT DERATING CURVE

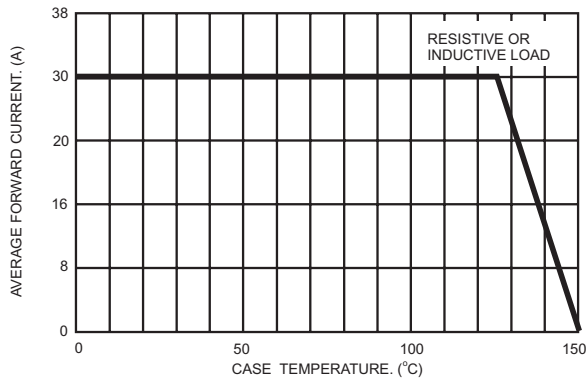


FIG.2- MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

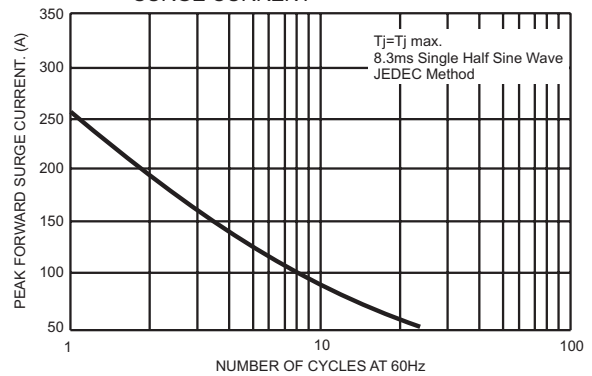


FIG.3- TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS

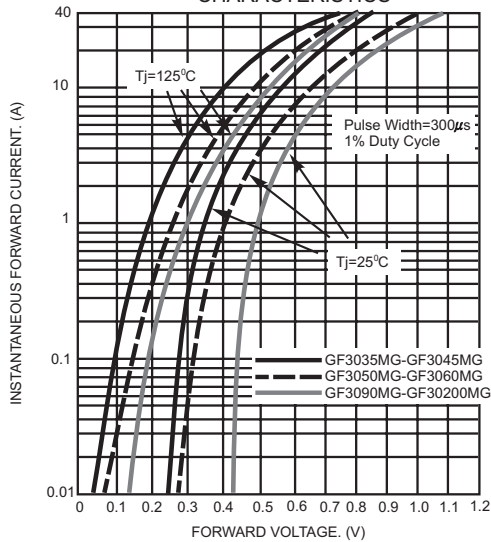


FIG.4- TYPICAL REVERSE CHARACTERISTICS

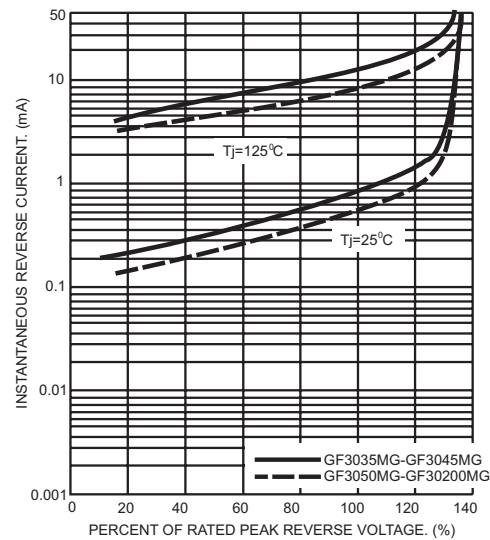


FIG.5- TYPICAL JUNCTION CAPACITANCE

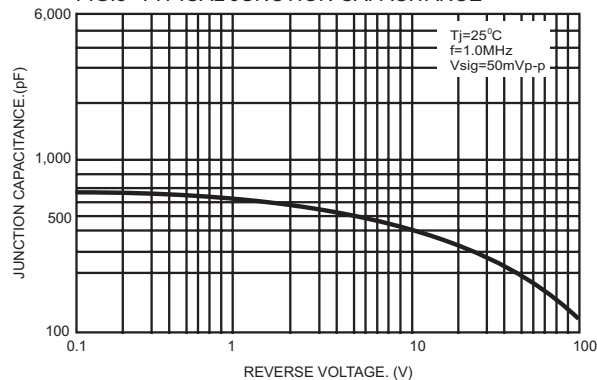


FIG.6- TYPICAL TRANSIENT THERMAL CHARACTERISTICS

